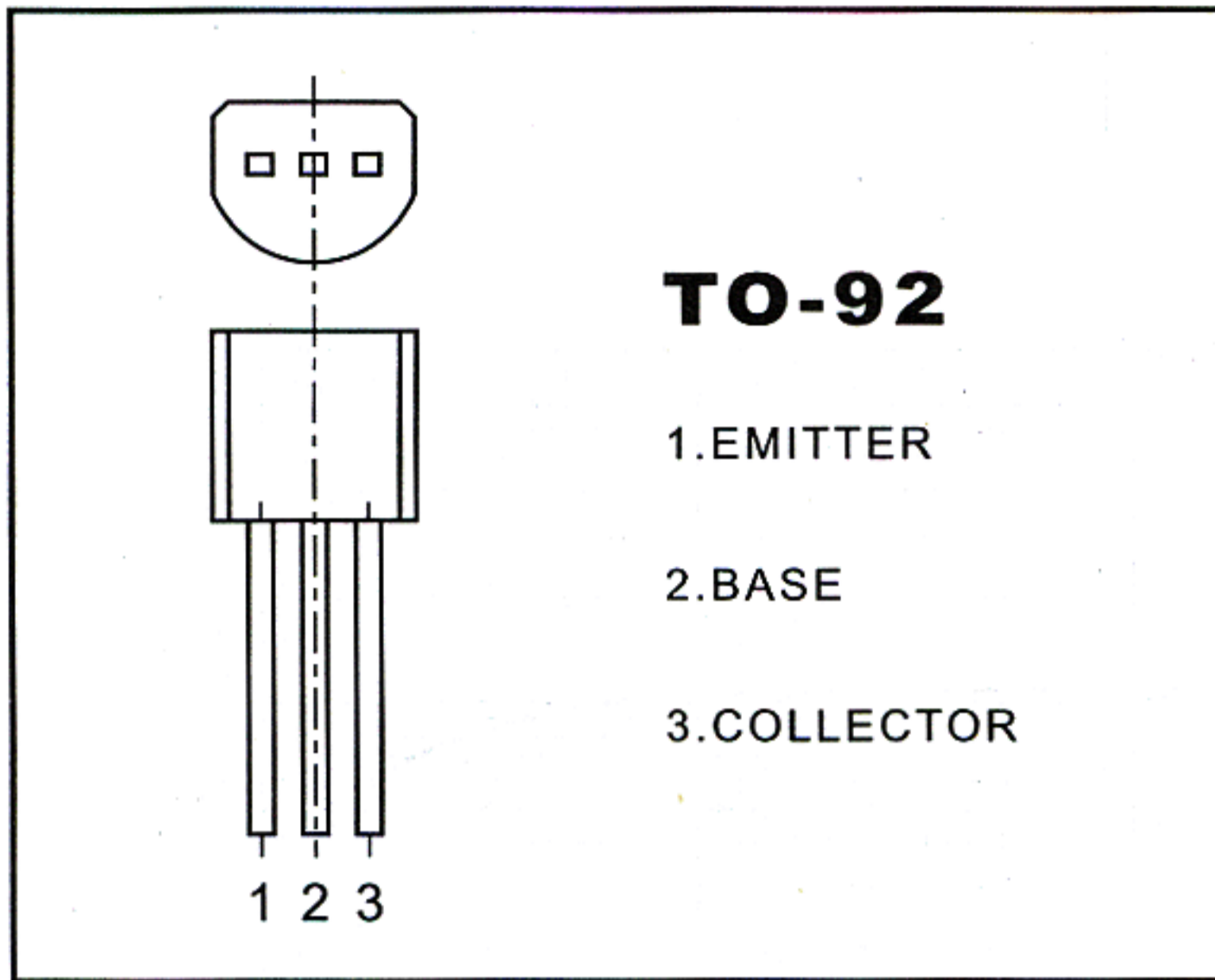


S8550 TRANSISTOR(PNP)



FEATURES

Power dissipation

P_{CM} : 0.625W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

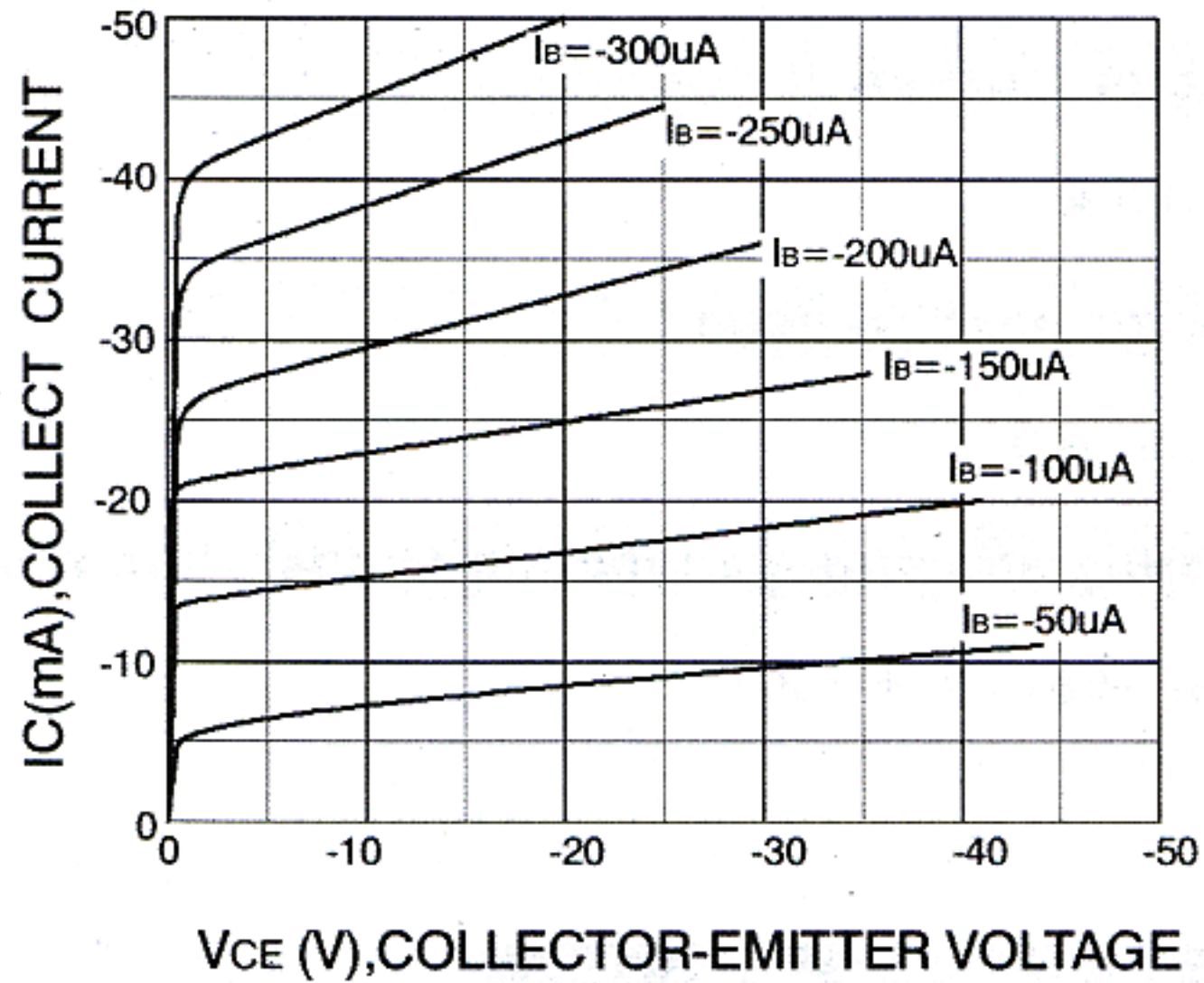
ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

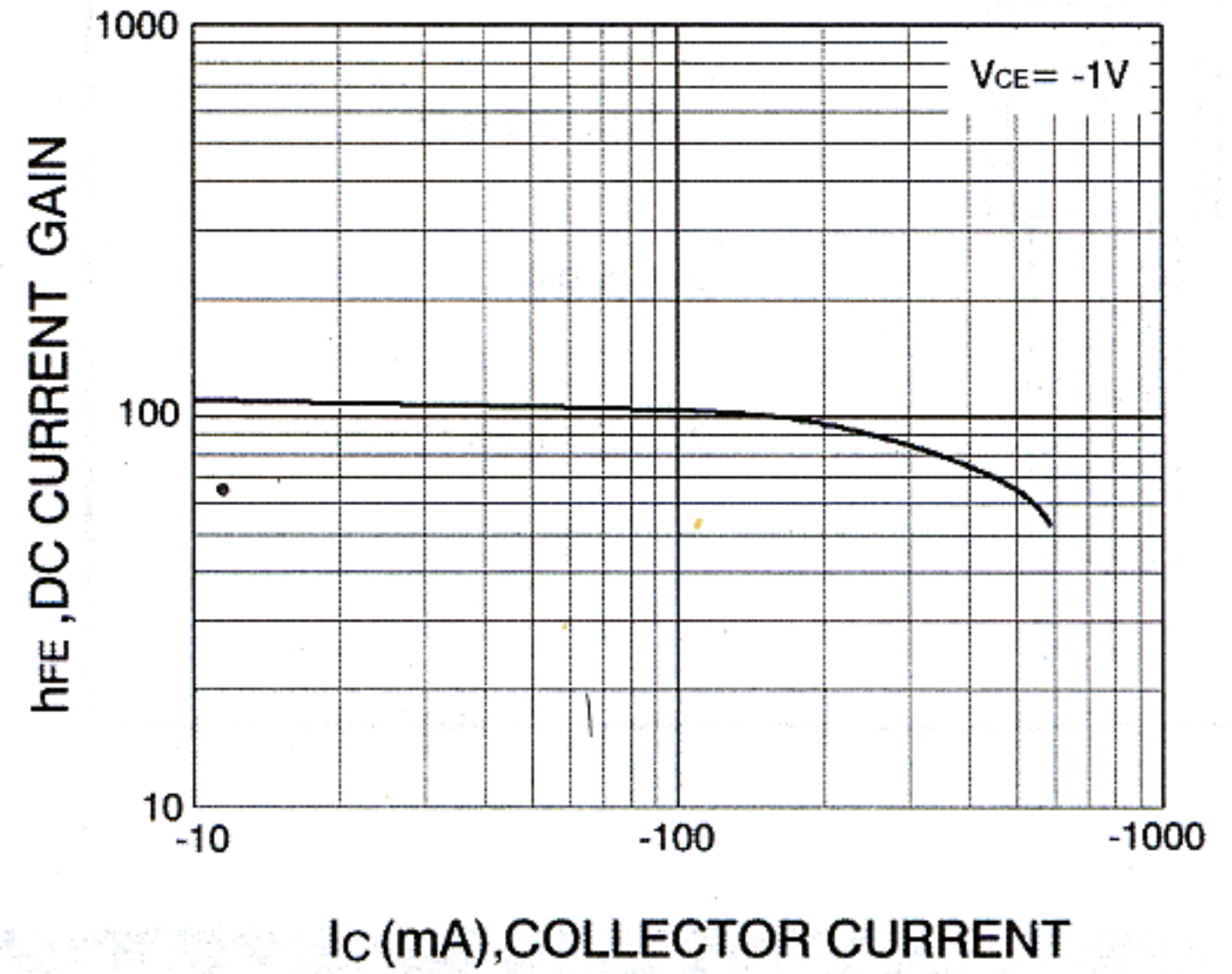
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1 mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40 V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20 V, I_B = 0$		-0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3 V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1 V, I_C = -50 mA$	85	300	
	$h_{FE(2)}$	$V_{CE} = -1 V, I_C = -500 mA$	50		
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -500 mA, I_B = -50 mA$		-0.6	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -500 mA, I_B = -50 mA$		-1.2	V
Base-emitter voltage	V_{BE}	$I_E = -100 mA$		-1.4	V
Transition frequency	f_t	$V_{CE} = -6 V, I_C = -20 mA$ $f = 30 MHz$	150		MHz

CLASSIFICATION OF $h_{FE(1)}$

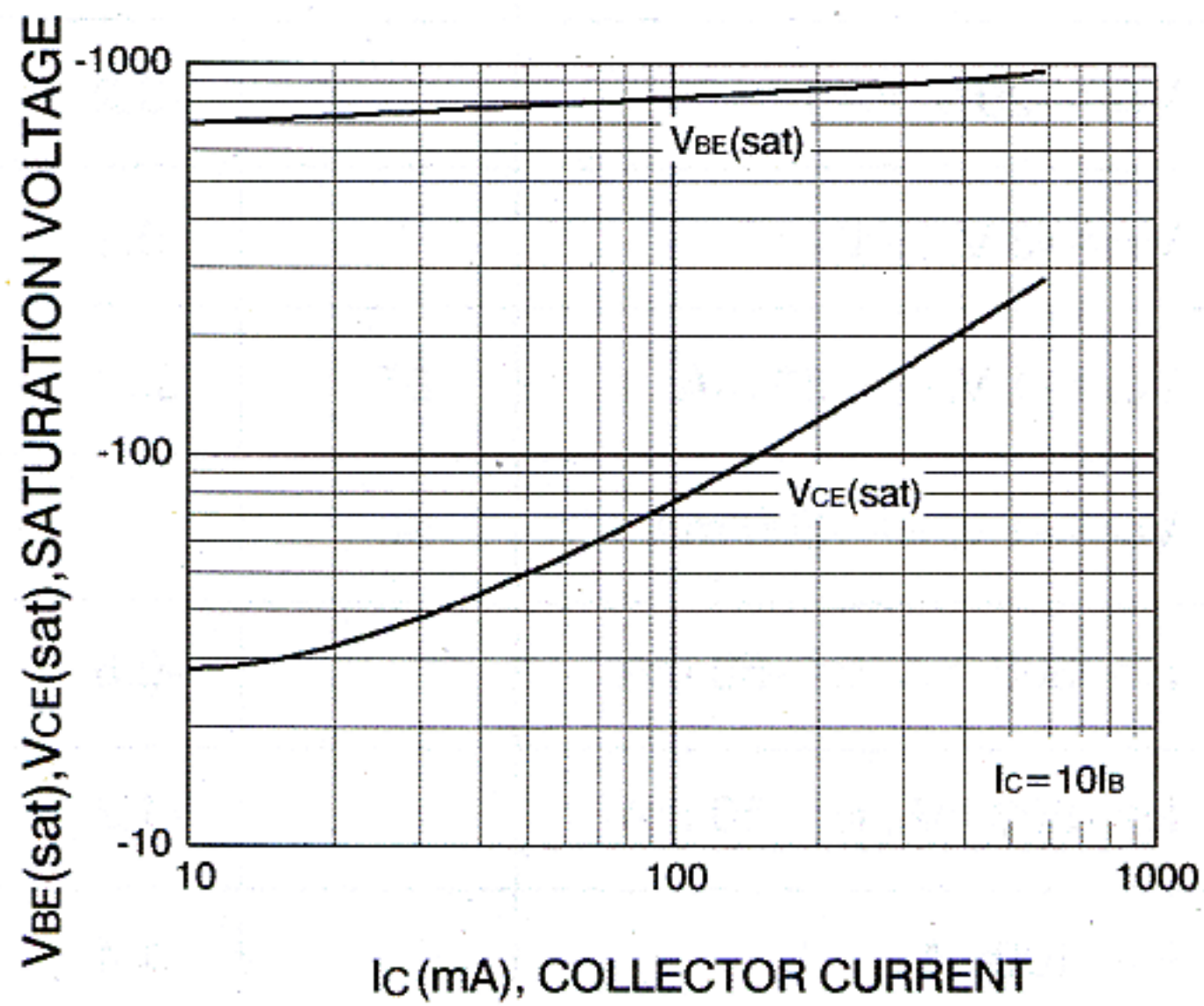
Rank	A	B	C
Range	85-160	120-200	160-300



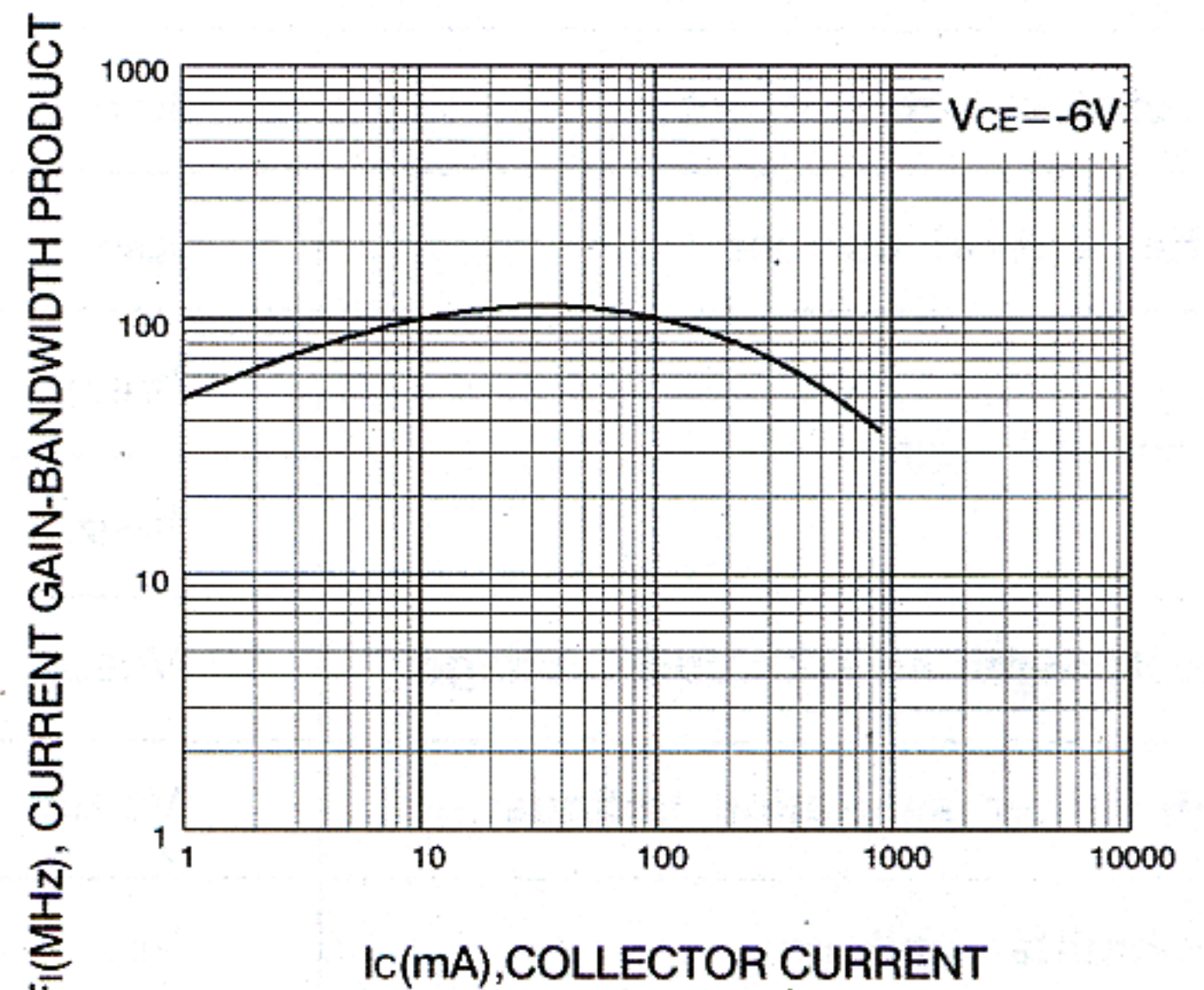
Static Characteristic



DC current Gain



**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**



Current Gain Bandwidth Product